

TwinDie™ 1.35V DDR3L SDRAM

MT41K2G4 – 128 Meg x 4 x 8 Banks x 2 Ranks

MT41K1G8 – 64 Meg x 8 x 8 Banks x 2 Ranks

Description

The 8Gb (TwinDie™) DDR3L SDRAM (1.35V) uses Micron’s 4Gb DDR3L SDRAM die (essentially two ranks of the 4Gb DDR3L SDRAM). Refer to Micron’s 4Gb DDR3 SDRAM data sheet for the specifications not included in this document. Specifications for base part number MT41K1G4 correlate to TwinDie manufacturing part number MT41K2G4; specifications for base part number MT41K512M8 correlate to TwinDie manufacturing part number MT41K1G8.

Features

- Uses 4Gb Micron die
- Two ranks (includes dual CS#, ODT, CKE, and ZQ balls)
- Each rank has eight internal banks for concurrent operation
- $V_{DD} = V_{DDQ} = 1.35V$ (1.283–1.45V); backward compatible to $V_{DD} = V_{DDQ} = 1.5V \pm 0.075V$
- 1.35V center-terminated push/pull I/O
- JEDEC-standard ball-out
- Low-profile package
- T_C of 0°C to 95°C
 - 0°C to 85°C: 8192 refresh cycles in 64ms
 - 85°C to 95°C: 8192 refresh cycles in 32ms
 - Industrial temperature (IT) available (Rev. E)

Options

- Configuration
 - 128 Meg x 4 x 8 banks x 2 ranks 2G4
 - 64 Meg x 8 x 8 banks x 2 ranks 1G8
- FBGA package (Pb-free)
 - 78-ball FBGA (10.5mm x 12mm x 1.2mm) Die Rev :D THE
 - 78-ball FBGA (9.5mm x 11.5mm x 1.2mm) Die Rev :E TRF
- Timing – cycle time¹
 - 1.071ns @ CL = 13 (DDR3L-1866) -107
 - 1.25ns @ CL = 11 (DDR3L-1600) -125
 - 1.5ns @ CL = 9 (DDR3L-1333) -15E
 - 1.87ns @ CL = 7 (DDR3L-1066) -187E
- Self refresh
 - Standard None
- Operating temperature
 - Commercial (0°C ≤ T_C ≤ 95°C) None
 - Industrial (-40°C ≤ T_C ≤ 95°C) Rev. E IT
- Revision :D/:E

Note: 1. CL = CAS (READ) latency.

Table 1: Key Timing Parameters

Speed Grade	Data Rate (MT/s)	Target ^t RCD- ^t RP-CL	^t RCD (ns)	^t RP (ns)	CL (ns)
-107 ^{1, 2, 3}	1866	13-13-13	13.91	13.91	13.91
-125 ^{1, 2}	1600	11-11-11	13.75	13.75	13.75
-15E ¹	1333	9-9-9	13.5	13.5	13.5
-187E	1066	7-7-7	13.1	13.1	13.1

- Notes: 1. Backward compatible to 1066, CL = 7 (-187E).
 2. Backward compatible to 1333, CL = 9 (-15E).
 3. Backward compatible to 1600, CL = 11 (-125).

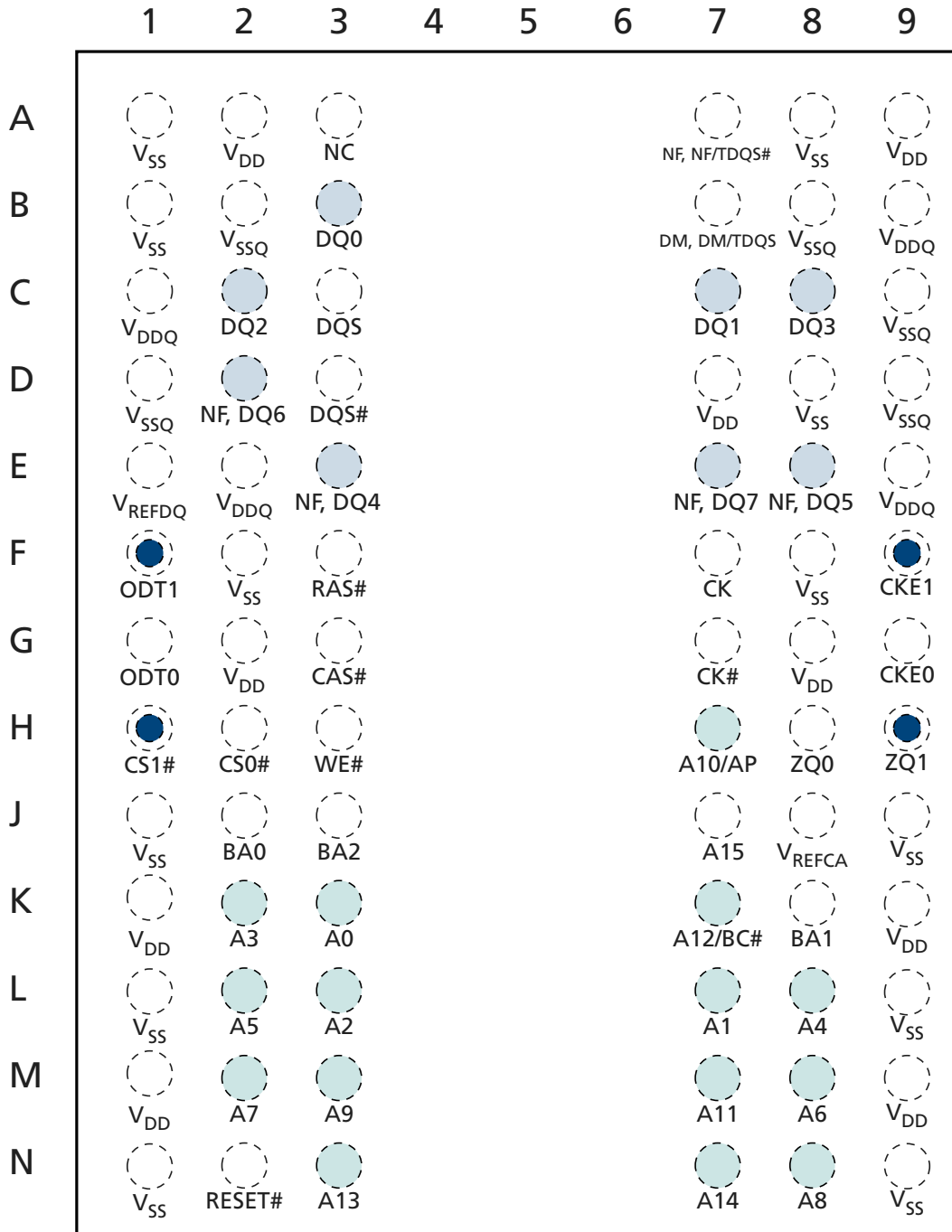


Table 2: Addressing

Parameter	2048 Meg x 4	1024 Meg x 8
Configuration	128 Meg x 4 x 8 banks x 2 ranks	64 Meg x 8 x 8 banks x 2 ranks
Refresh count	8K	8K
Row address	64K A[15:0]	64K A[15:0]
Bank address	8 BA[2:0]	8 BA[2:0]
Column address	2K A[11, 9:0]	1K A[9:0]

Ball Assignments and Descriptions

Figure 1: 78-Ball FBGA Ball Assignments (Top View)



Note: 1. Dark balls (with ring) designate balls that differ from the monolithic versions.

Table 3: FBGA 78-Ball Descriptions

Symbol	Type	Description
A15, A14, A13, A12/BC#, A11, A10/AP, A[9:0]	Input	Address inputs: Provide the row address for ACTIVATE commands, and the column address and auto precharge bit (A10) for READ/WRITE commands, to select one location out of the memory array in the respective bank. A10 sampled during a PRECHARGE command determines whether the PRECHARGE applies to one bank (A10 LOW, bank selected by BA[2:0]) or all banks (A10 HIGH). The address inputs also provide the op-code during a LOAD MODE command. Address inputs are referenced to V_{REFCA} . A12/BC#: When enabled in the mode register (MR), A12 is sampled during READ and WRITE commands to determine whether burst chop (on-the-fly) will be performed (HIGH = burst length (BL) of 8 or no burst chop, LOW = burst chop (BC) of 4, burst chop).
BA[2:0]	Input	Bank address inputs: BA[2:0] define the bank to which an ACTIVATE, READ, WRITE, or PRECHARGE command is being applied. BA[2:0] define which mode register (MR0, MR1, MR2, or MR3) is loaded during the LOAD MODE command. BA[2:0] are referenced to V_{REFCA} .
CK, CK#	Input	Clock: CK and CK# are differential clock inputs. All command, address, and control input signals are sampled on the crossing of the positive edge of CK and the negative edge of CK#. Output data strobe (DQS, DQS#) is referenced to the crossings of CK and CK#.
CKE[1:0]	Input	Clock enable: CKE enables (registered HIGH) and disables (registered LOW) internal circuitry and clocks on the DRAM. The specific circuitry that is enabled/disabled is dependent upon the DDR3L SDRAM configuration and operating mode. Taking CKE LOW provides PRECHARGE power-down and SELF REFRESH operations (all banks idle) or active power-down (row active in any bank). CKE is synchronous for power-down entry and exit and for self refresh entry. CKE is asynchronous for self refresh exit. Input buffers (excluding CK, CK#, CKE, RESET#, and ODT) are disabled during power-down. Input buffers (excluding CKE and RESET#) are disabled during SELF REFRESH. CKE is referenced to V_{REFCA} .
CS#[1:0]	Input	Chip select: CS# enables (registered LOW) and disables (registered HIGH) the command decoder. All commands are masked when CS# is registered HIGH. CS# provides for external rank selection on systems with multiple ranks. CS# is considered part of the command code.
DM	Input	Input data mask: DM is an input mask signal for write data. Input data is masked when DM is sampled HIGH, along with the input data, during a write access. Although the DM ball is input-only, the DM loading is designed to match that of the DQ and DQS balls. DM is referenced to V_{REFDQ} . DM has an optional use as TDQS on the x8.
ODT[1:0]	Input	On-die termination: ODT enables (registered HIGH) and disables (registered LOW) termination resistance internal to the DDR3L SDRAM. When enabled in normal operation, ODT is only applied to each of the following balls: DQ[7:0], DQS, DQS#, and DM for the x8; DQ[3:0], DQS, DQS#, and DM for the x4. The ODT input is ignored if disabled via the LOAD MODE command. ODT is referenced to V_{REFCA} .
RAS#, CAS#, WE#	Input	Command inputs: RAS#, CAS#, and WE# (along with CS#) define the command being entered and are referenced to V_{REFCA} .
RESET#	Input	Reset: RESET# is an active LOW CMOS input referenced to V_{SS} . The RESET# input receiver is a CMOS input defined as a rail-to-rail signal with DC HIGH $\geq 0.8 \times V_{DDQ}$ and DC LOW $\leq 0.2 \times V_{DDQ}$. RESET# assertion and desertion are asynchronous.
DQ[3:0]	I/O	Data input/output: Bidirectional data bus for x4 configuration. DQ[3:0] are referenced to V_{REFDQ} .

Table 3: FBGA 78-Ball Descriptions (Continued)

Symbol	Type	Description
DQ[7:0]	I/O	Data input/output: Bidirectional data bus for x8 configuration. DQ[7:0] are referenced to V_{REFDQ} .
DQS, DQS#	I/O	Data strobe: DQS and DQS# are differential data strobes: Output with read data; edge aligned with read data; input with write data; center-aligned with write data.
TDQS, TDQS#	I/O	Termination data strobe: Applies to the x8 configuration only. When TDQS is enabled, DM is disabled, and the TDQS and TDQS# balls provide termination resistance.
V_{DD}	Supply	Power supply: 1.35V (1.283V to 1.45V operational; compatible with 1.5V operation)
V_{DDQ}	Supply	DQ power supply: 1.35V (1.283V to 1.45V operational; compatible with 1.5V operation). Isolated on the device for improved noise immunity.
V_{REFCA}	Supply	Reference voltage for control, command, and address: V_{REFCA} must be maintained at all times (including self refresh) for proper device operation.
V_{REFDQ}	Supply	Reference voltage for data: V_{REFDQ} must be maintained at all times (including self refresh) for proper device operation.
V_{SS}	Supply	Ground.
V_{SSQ}	Supply	DQ ground: Isolated on the device for improved noise immunity.
ZQ[1:0]	Reference	External reference ball for output drive calibration: This ball is tied to an external 240 Ω resistor (RZQ), which is tied to V_{SSQ} .
NC	–	No connect: These balls should be left unconnected (the ball has no connection to the DRAM or to other balls).
NF	–	No function: When configured as a x4 device, these balls are NF. When configured as a x8 device, these balls are defined as TDQS#, DQ[7:4].

Functional Description

The TwinDie DDR3L SDRAM is a high-speed, CMOS dynamic random access memory device internally configured as two 8-bank DDR3L SDRAM devices.

Although each die is tested individually within the dual-die package, some TwinDie test results may vary from a like die tested within a monolithic die package.

The DDR3L SDRAM uses a double data rate architecture to achieve high-speed operation. The double data rate architecture is an $8n$ -prefetch architecture with an interface designed to transfer two data words per clock cycle at the I/O balls. A single read or write access consists of a single $8n$ -bit-wide, one-clock-cycle data transfer at the internal DRAM core and eight corresponding n -bit-wide, one-half-clock-cycle data transfers at the I/O balls.

The differential data strobe (DQS, DQS#) is transmitted externally, along with data, for use in data capture at the DDR3L SDRAM input receiver. DQS is center-aligned with data for WRITES. The read data is transmitted by the DDR3L SDRAM and edge-aligned to the data strobes.

Read and write accesses to the DDR3L SDRAM are burst-oriented. Accesses start at a selected location and continue for a programmed number of locations in a programmed sequence. Accesses begin with the registration of an ACTIVATE command, which is then followed by a READ or WRITE command. The address bits registered coincident with the ACTIVATE command are used to select the bank and row to be accessed. The address bits (including $CSn\#$, BA_n , and A_n) registered coincident with the READ or WRITE command are used to select the rank, bank, and starting column location for the burst access.

This data sheet provides a general description, package dimensions, and the package ballout. Refer to the Micron monolithic DDR3L data sheet for complete information regarding individual die initialization, register definition, command descriptions, and die operation.

Industrial Temperature

The industrial temperature (IT) option, if offered, requires that the case temperature not exceed -40°C or 95°C . JEDEC specifications require the refresh rate to double when T_C exceeds 85°C ; this also requires use of the high-temperature self refresh option. Additionally, ODT resistance, I_{DD} values, some IDD specifications and the input/output impedance must be derated when T_C is $< 0^{\circ}\text{C}$ or $> 95^{\circ}\text{C}$. See the DDR3 monolithic data sheet for details.

Functional Block Diagrams

Figure 2: Functional Block Diagram (128 Meg x 4 x 8 Banks x 2 Ranks)

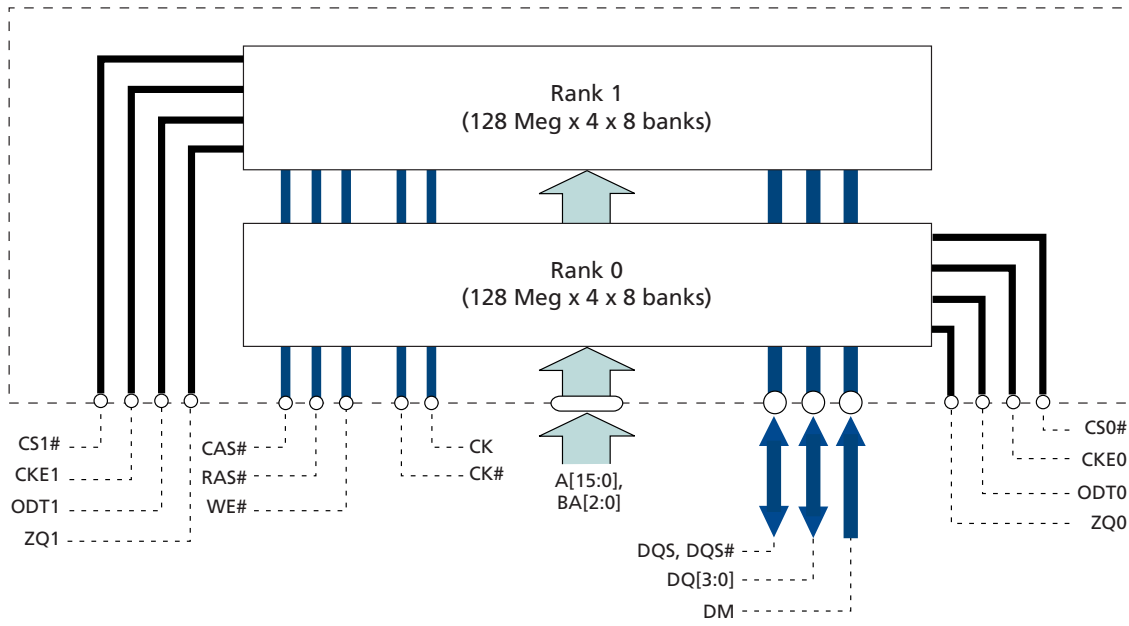
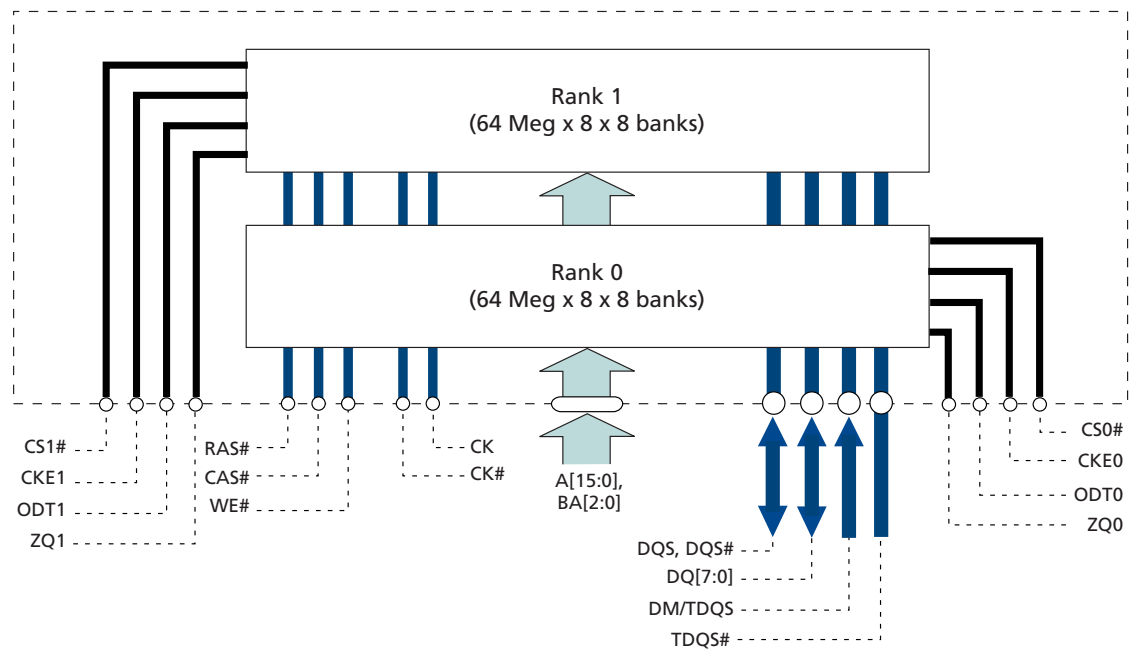


Figure 3: Functional Block Diagram (64 Meg x 8 x 8 Banks x 2 Ranks)



Electrical Specifications – Absolute Ratings

Stresses greater than those listed may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions outside those indicated in the device data sheet is not implied. Exposure to absolute maximum rating conditions for extended periods may adversely affect reliability.

Table 4: Absolute Maximum DC Ratings

Parameter	Symbol	Min	Max	Units	Notes
V_{DD} supply voltage relative to V_{SS}	V_{DD}	-0.4	1.975	V	1
V_{DD} supply voltage relative to V_{SSQ}	V_{DDQ}	-0.4	1.975	V	
Voltage on any ball relative to V_{SS}	V_{IN}, V_{OUT}	-0.4	1.975	V	
Input leakage current Any input $0V \leq V_{IN} \leq V_{DD}$, V_{REF} pin $0V \leq V_{IN} \leq 1.1V$ (All other pins not under test = 0V)	I_I	-4	4	μA	
V_{REF} supply leakage current $V_{REFDQ} = V_{DD}/2$ or $V_{REFCA} = V_{DD}/2$ (All other pins not under test = 0V)	I_{VREF}	-2	2	μA	2
Operating case temperature	T_C	0	95	$^{\circ}C$	3, 4
Storage temperature	T_{STG}	-55	150	$^{\circ}C$	

- Notes:
- V_{DD} and V_{DDQ} must be within 300mV of each other at all times, and V_{REF} must not be greater than $0.6 \times V_{DDQ}$. When V_{DD} and V_{DDQ} are less than 500mV, V_{REF} may be $\leq 300mV$.
 - The minimum limit requirement is for testing purposes. The leakage current on the V_{REF} pin should be minimal.
 - MAX operating case temperature. T_C is measured in the center of the package (see Figure 4 (page 9)).
 - Device functionality is not guaranteed if the DRAM device exceeds the maximum T_C during operation.

Temperature and Thermal Impedance

It is imperative that the DDR3L SDRAM device's temperature specifications, shown in the following table, be maintained in order to ensure the junction temperature is in the proper operating range to meet data sheet specifications. An important step in maintaining the proper junction temperature is using the device's thermal impedances correctly. The thermal impedances listed in Table 6 (page 9) apply to the current die revision and packages.

Incorrectly using thermal impedances can produce significant errors. Read Micron technical note TN-00-08, "Thermal Applications," prior to using the values listed in the thermal impedance table. For designs that are expected to last several years and require the flexibility to use several DRAM die shrinks, consider using final target theta values (rather than existing values) to account for increased thermal impedances from the die size reduction.

The DDR3L SDRAM device's safe junction temperature range can be maintained when the T_C specification is not exceeded. In applications where the device's ambient temperature is too high, use of forced air and/or heat sinks may be required to satisfy the case temperature specifications.

Table 5: Thermal Characteristics

Notes 1–3 apply to entire table

Parameter	Symbol	Value	Units	Notes
Operating temperature	T_C	0 to 85	°C	
		0 to 95	°C	4

- Notes:
1. MAX operating case temperature T_C is measured in the center of the package, as shown below.
 2. A thermal solution must be designed to ensure that the device does not exceed the maximum T_C during operation.
 3. Device functionality is not guaranteed if the device exceeds maximum T_C during operation.
 4. If T_C exceeds 85°C, the DRAM must be refreshed externally at 2x refresh, which is a 3.9µs interval refresh rate. The use of self refresh temperature (SRT) or automatic self refresh (ASR), if available, must be enabled.

Figure 4: Temperature Test Point Location

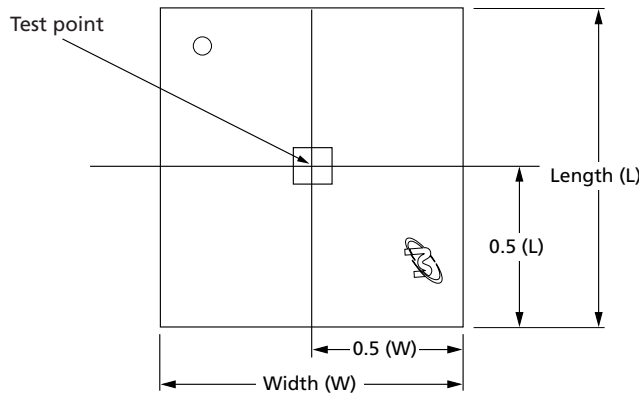


Table 6: Thermal Impedance

Die Rev	Package	Substrate	Θ_{JA} (°C/W) Airflow = 0m/s	Θ_{JA} (°C/W) Airflow = 1m/s	Θ_{JA} (°C/W) Airflow = 2m/s	Θ_{JB} (°C/W)	Θ_{JC} (°C/W)	Notes
D	78-ball	Low Con- ductivity	55.7	42.3	36.8	32	1.5	1
		High Con- ductivity	35.6	29.3	26.7	23.9		
E	78-ball	Low Con- ductivity	57.7	44.1	38.8	20.5	2.1	1
		High Con- ductivity	36.7	30.6	28.1	18.6		

- Note: 1. Thermal resistance data is based on a number of samples from multiple lots and should be viewed as a typical number.



Electrical Specifications – I_{CDD} Parameters

Table 7: DDR3L I_{CDD} Specifications and Conditions (Rev D)

Note 1 applies to the entire table

Combined Symbol	Individual Die Status	Bus Width	-187E	-15E	-125	Units
I _{CDD0}	I _{CDD0} = I _{DD0} + I _{DD2P0}	x4, x8	75	80	90	mA
I _{CDD1}	I _{CDD1} = I _{DD1} + I _{DD2P0}	x4	85	90	95	mA
		x8	92	97	102	
I _{CDD2P0} (slow exit)	I _{CDD2P0} = I _{DD2P0} + I _{DD2P0}	x4, x8	30	30	30	mA
I _{CDD2P1} (fast exit)	I _{CDD2P1} = I _{DD2P1} + I _{DD2P0}	x4, x8	43	45	50	mA
I _{CDD2Q}	I _{CDD2Q} = I _{DD2Q} + I _{DD2P0}	x4, x8	52	57	62	mA
I _{CDD2N}	I _{CDD2N} = I _{DD2N} + I _{DD2P0}	x4, x8	54	57	62	mA
I _{CDD2N T}	I _{CDD2NT} = I _{DD2NT} + I _{DD2P0}	x4, x8	55	60	65	mA
I _{CDD3P}	I _{CDD3P} = I _{DD3P} + I _{DD2P0}	x4, x8	60	65	70	mA
I _{CDD3N}	I _{CDD3N} = I _{DD3N} + I _{DD2P0}	x4, x8	62	67	72	mA
I _{CDD4R}	I _{CDD4RCDD4R} = I _{DD4R} + I _{DD2P0}	x4	140	160	180	mA
		x8	152	172	192	
I _{CDD4W}	I _{CDD4W} = I _{DD4W} + I _{DD2P0}	x4	120	140	160	mA
		x8	130	150	170	
I _{CDD5B}	I _{CDD5B} = I _{DD5B} + I _{DD2P0}	x4, x8	215	220	230	mA
I _{CDD6}	I _{CDD6} = I _{DD6} + I _{DD6}	x4, x8	36	36	36	mA
I _{CDD6ET}	I _{CDD6ET} = I _{DD6ET} + I _{DD6ET}	x4, x8	48	48	48	mA
I _{CDD7}	I _{CDD7} = I _{DD7} + I _{DD2P0}	x4, x8	215	255	295	mA
I _{CDD8}	I _{CDD8} = 2 × I _{DD2P0} + 4	x4, x8	34	34	34	mA

Note: 1. I_{CDD} values reflect the combined current of both individual die. I_{DDx} represents individual die values.



Table 8: DDR3L I_{CDD} Specifications and Conditions (Rev E)

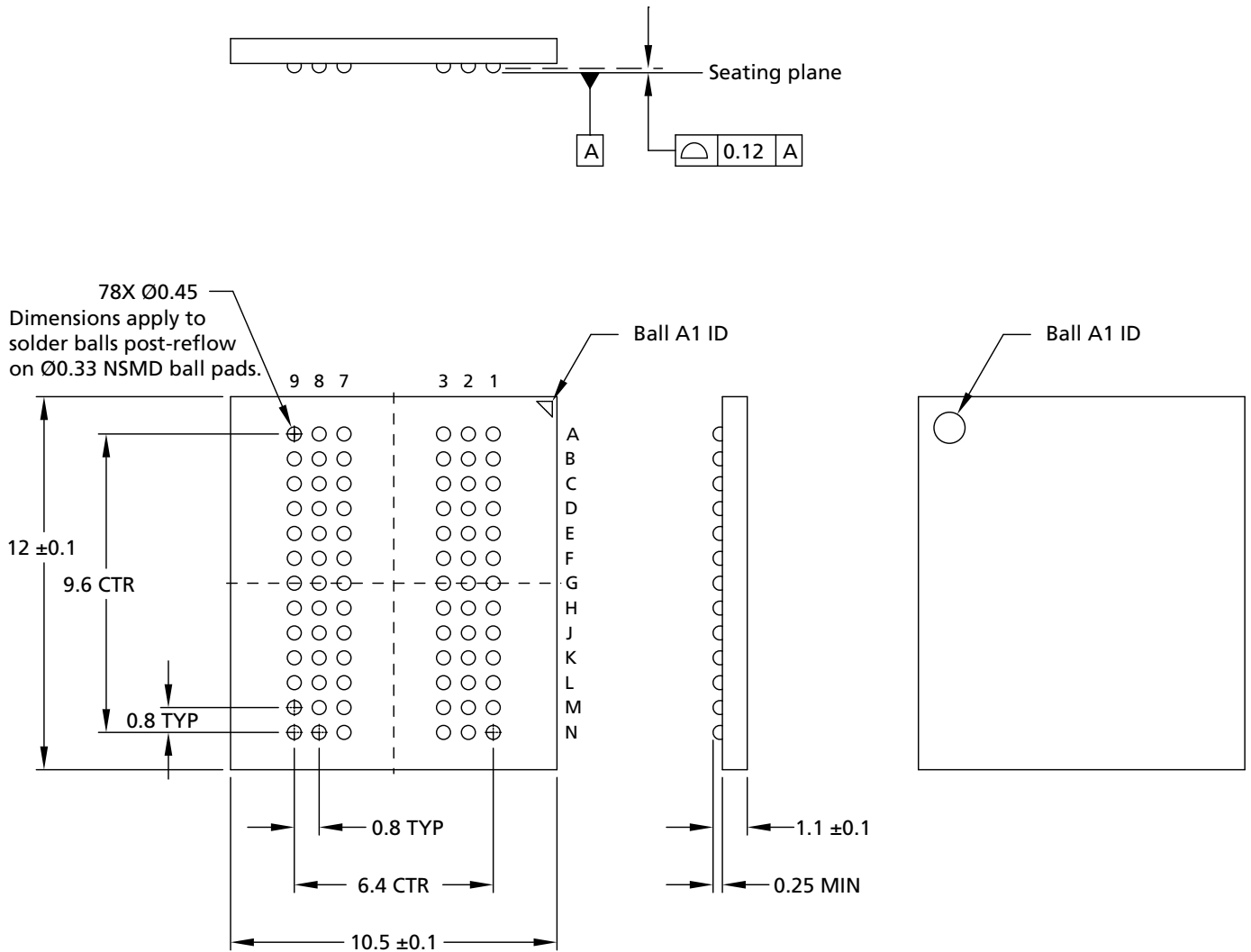
Note 1 applies to the entire table

Combined Symbol	Individual Die Status	Bus Width	-187E	-15E	-125	-107	Units
I _{CDD0}	I _{CDD0} = I _{DD0} + I _{DD2P0} + 5	x4, x8	67	70	78	85	mA
I _{CDD1}	I _{CDD1} = I _{DD1} + I _{DD2P0} + 5	x4	76	80	84	88	mA
		x8	82	85	89	93	
I _{CDD2P0} (slow exit)	I _{CDD2P0} = I _{DD2P0} + I _{DD2P0}	x4, x8	36	36	36	36	mA
I _{CDD2P1} (fast exit)	I _{CDD2P1} = I _{DD2P1} + I _{DD2P0}	x4, x8	44	46	50	55	mA
I _{CDD2Q}	I _{CDD2Q} = I _{DD2Q} + I _{DD2P0}	x4, x8	45	46	50	53	mA
I _{CDD2N}	I _{CDD2N} = I _{DD2N} + I _{DD2P0}	x4, x8	46	47	50	53	mA
I _{CDD2N T}	I _{CDD2NT} = I _{DD2NT} + I _{DD2P0}	x4, x8	50	53	57	60	mA
I _{CDD3P}	I _{CDD3P} = I _{DD3P} + I _{DD2P0}	x4, x8	50	53	56	59	mA
I _{CDD3N}	I _{CDD3N} = I _{DD3N} + I _{DD2P0}	x4, x8	50	53	56	59	mA
I _{CDD4R}	I _{CDD4RCDD4R} = I _{DD4R} + I _{DD2P0} + 5	x4	136	153	170	187	mA
		x8	146	163	180	197	
I _{CDD4W}	I _{CDD4W} = I _{DD4W} + I _{DD2P0} + 5	x4	110	126	141	156	mA
		x8	118	133	148	164	
I _{CDD5B}	I _{CDD5B} = I _{DD5B} + I _{DD2P0}	x4, x8	242	246	253	260	mA
I _{CDD6}	I _{CDD6} = I _{DD6} + I _{DD6}	x4, x8	40	40	40	40	mA
I _{CDD6ET}	I _{CDD6ET} = I _{DD6ET} + I _{DD6ET}	x4, x8	50	50	50	50	mA
I _{CDD7}	I _{CDD7} = I _{DD7} + I _{DD2P0} + 5	x4, x8	183	213	243	274	mA
I _{CDD8}	I _{CDD8} = 2 × I _{DD2P0} + 4	x4, x8	40	40	40	40	mA

Note: 1. I_{CDD} values reflect the combined current of both individual die. I_{DDx} represents individual die values.

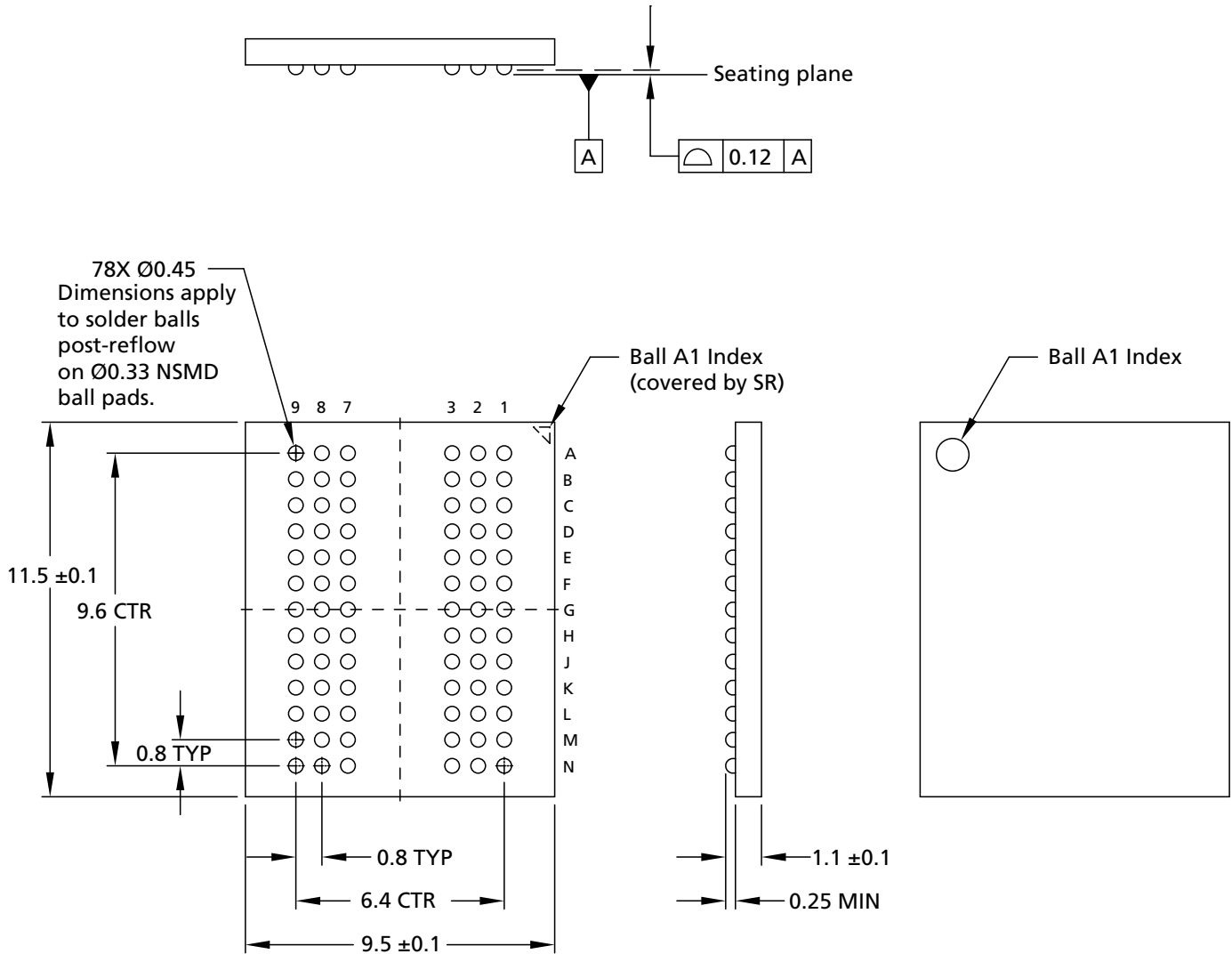
Package Dimensions

Figure 5: 78-Ball FBGA Die Rev. D (package code THE)



- Notes: 1. All dimensions are in millimeters.
2. Solder ball material: SAC305 (96.5% Sn, 3% Ag, 0.5% Cu).

Figure 6: 78-Ball FBGA Die Rev. E (package code TRF)



- Notes: 1. All dimensions are in millimeters.
 2. Solder ball material: SAC305 (96.5% Sn, 3% Ag, 0.5% Cu).

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This data sheet contains minimum and maximum limits specified over the power supply and temperature range set forth herein. Although considered final, these specifications are subject to change, as further product development and data characterization sometimes occur.